

### **Amendments to the Abstract**

Please replace paragraph [0036] with the following amended paragraph:

A method is disclosed for forming a thin film ~~field-effect~~ transistor. A photoresist layer is formed on top of the preliminary substrate. A portion of the photoresist layer is selectively removed in a single exposure process to form a photoresist pattern having a two-portion structure with a first portion having a first width and a second portion underneath the first portion with a second width. Such a photoresist pattern helps to reduce the number of mask processes used for forming the thin film ~~field-effect~~ transistor.

### CONCLUSION

Paragraphs 0002, 0014, 0020, claims 1, 7, 14 and the Abstract have been amended to delete the words "field effect".

No new matter is added.

In view of the foregoing amendments and remarks, Applicant submits that this application is in condition for examination.

The Assistant Commissioner for Patents is hereby authorized to charge any additional fees or credit any excess payment that may be associated with this communication to deposit account 04-1679 (Reference E0523-00040).

Respectfully submitted,

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